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** CONTINUING DATA ***** *Ac*

This application is a DIV of 10/330,180 12/30/2002 PAT 6,716,752 *Ac*
 which is a CON of 09/977,505 10/16/2001 PAT 6,627,545 *Ac*
 which is a CON of 09/430,037 10/29/1999 PAT 6,337,292 *Ac*

** FOREIGN APPLICATIONS *****

JAPAN 1998-309237 10/29/1998 *Ac*

IF REQUIRED, FOREIGN FILING LICENSE GRANTED
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|-----------------------------------------------------------------------------------------------------------------------------------------------------------|-------------------------------------------------|------------------------|----------------------|----------------------------|
| Foreign Priority claimed <input checked="" type="checkbox"/> yes <input type="checkbox"/> no | STATE OR COUNTRY KOREA, REPUBLIC OF | SHEETS DRAWING 8 | TOTAL CLAIMS 7 | INDEPENDENT CLAIMS 1 |
| 35 USC 119 (a-d) conditions met <input checked="" type="checkbox"/> yes <input type="checkbox"/> no <input type="checkbox"/> Met after Allowance | | | | |
| Verified and Acknowledged Examiner's Signature <i>[Signature]</i> Initials <i>[Initials]</i> | | | | |

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TITLE
 Method of forming silicon oxide layer and method of manufacturing thin film transistor thereby

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| <input type="checkbox"/> All Fees |
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